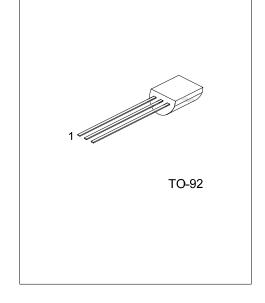
MCR101 SCR

SENSITIVE GATE SILICON CONTROLLED RECTIFIERS REVERSE BLOCKING **THYRISTORS**

DESCRIPTION

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thrusters, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92 package which is readily adaptable for use in automatic insertion equipment.



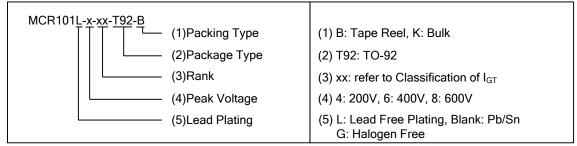
FEATURES

- *Sensitive Gate Allows Triggering by Micro Controllers and other Logic Circuits
- *Blocking Voltage to 600V
- *On-State Current Rating of 0.8A RMS at 80°C
- *High Surge Current Capability 10A
- *Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- *Immunity to dV/dt 20V/µsec Minimum at 110°C
- *Glass-Passivated Surface for Reliability and Uniformity

ORDERING INFORMATION

Ordering Number			Daakaga	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing
MCR101-x-xx-T92-B	MCR101L-x-xx-T92-B	MCR101G-x-xx-T92-B	TO-92	G	Α	K	Tape Box
MCR101-x-xx-T92-K	MCR101L-x-xx-T92-K	MCR101G-x-xx-T92-K	TO-92	G	Α	K	Bulk

Note: Pin Assignment: G: Gate A: Anode K: Cathode



www.unisonic.com.tw 1 of 5 QW-R301-009,D

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Peak Repetitive Off-State Voltage(note)	MCR101-4		200	
(T _J =-40 to 110°C, Sine Wave, 50 to 60Hz; Gate	MCR101-6	V_{DRM}, V_{RRM}	400	V
Open)	MCR101-8		600	
On-Sate RMS Current (Tc=80°C) 180° Condition	Angles	I _{T(RMS)}	0.8	Α
Peak Non-Repetitive Surge Current			40	^
(1/2 cycle, Sine Wave, 60Hz, T _J =25°C)	I _{TSM}	10	Α	
Circuit Fusing Considerations (t=8.3 ms)	l ² t	0.415	A^2s	
Forward Peak Gate Power (T _A =25°C, Pulse Width	P_GM	0.1	W	
Forward Average Gate Power (T _A =25°C, t=8.3ms	$P_{G(AV)}$	0.1	W	
Peak Gate Current – Forward (T _A =25°C, Pulse W	I _{GM}	1	Α	
Peak Gate Voltage – Reverse (T _A =25°C, Pulse W	V_{GRM}	5	V	
Operating Junction Temperature @ Rated V _{RRM} a	T_J	-40 ~ +110	°C	
Storage Temperature	T _{STG}	-40 ~ +150	°C	

Note: V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT	
Junction to Ambient	θ_{JA}	200	°C/W	
Junction to Case	θ_{JC}	75	°C/W	

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise stated)

		I		MIN			
PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS							
Peak Forward or Reverse	Tc=25°C	<u> </u>	I_{DRM} , I_{RRM} V_D =Rated V_{DRM} and V_{RRM} ; R_{GK} =1k Ω			10	
Blocking Current	Tc=125°C	IDRM, IRRM				100	μΑ
ON CHARACTERISTICS							
Peak Forward On-State Voltage (Note1) V _{TM}			I _{TM} =1A Peak @ T _A =25°C	1A Peak @ T _A =25°C		1.7	V
Gate Trigger Current (Continuous dc)(note2)		I _{GT}	V _{AK} =7Vdc, R _L =100Ω, T _C =25°C		40	200	μА
Holding Current (note 3)	Tc=25 °C	I _H	\/ -7\/da initiation a compant 2000 A		0.5	5	m A
	Tc=-40 °C		V _{AK} =7Vdc, initiating current=20mA			10	mA
Latch Current	Tc=25°C		\/ =7\/ a=200\		0.6	10	mΛ
	Tc=-40 °C	IL.	V _{AK} =7V, Ig=200μA			15	mA
Gate Trigger Current	Tc=25 °C	\/	V _{AK} =7Vdc, R _L =100Ω		0.62	0.8	V
(continuous dc) (Note 2)	Tc=-40 °C	$V_{\rm GT}$				1.2	V
DYNAMIC CHARACTERISTI	CS			•		•	
Critical Rate of Rise of Off-State Voltage		dV/dt	V_D =Rated V_{DRM} , Exponential Waveform, R_{GK} =1000 Ω , T_J =110°C		35		V/μs
		a v/at			- 30		ν,μο
Critical Rate of Rise of On-State Current		dı/dt	I _{PK} =20A, Pw=10μsec			50	Λ/ς
			diG/dt=1A/μsec, Igt=20mA			50	A/μs

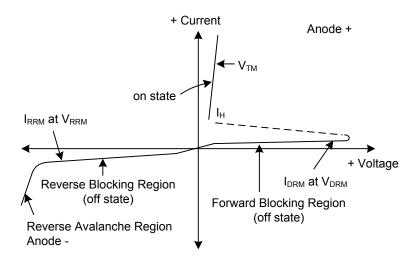
Notes: 1. Indicates Pulse Test Width≤1.0ms, duty cycle ≤1%

- 2. $R_{\text{GK}}\text{=}1000\Omega$ included in measurement.
- 3. Does not include R_{GK} in measurement.

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■ VOLTAGE CURRENT CHARACTERISTIC OF SCR

SYMBOL	PARAMETER
V_{DRM}	Peak Repetitive Off Stat Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I _H	Holding Current



■ CLASSIFICATION OF I_{GT}

RANK	В	С	AA	AB	AC	AD
RANGE	48~105μA	95~200μΑ	8~16μA	14~21μA	19~25μA	23~52μA

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■ TYPICAL CHARACTERISTICS

Figure 1. Typical Gate Trigger Current versus Junction Temperature

100
90
40
30
20
10
-40 -25 -10 5 20 25 50 65 80 95 110
Junction Temperature, T_J (°C)

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

1.0

(\$\frac{1}{2}\text{O}

Figure 3. Typical Holding Current versus Junction Temperature

1000

(V 1)

100

-40 -25 -10 5 20 25 50 65 80 95 110

Junction Temperature, T_J (°C)

Figure 4. Typical Latching Current versus Junction Temperature

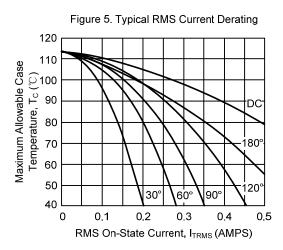
1000

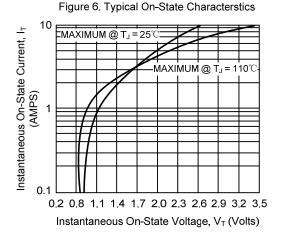
(V 1)

100

-40 -25 -10 5 20 25 50 65 80 95 110

Junction Temperature, T_J (°C)





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